

Product Overview

FGA5065ADF: IGBT, 650 V, 50 A Field Stop Trench

For complete documentation, see the data sheet.

This ADF IGBT series adopted field stop trench 3rd generation IGBT which offer extreme low $V_{CE(sat)}$ and much faster switching characteristics for outstanding efficiency. And this kind of technology is fully optimized to variety PFC (Power Factor Correction) topology; Single Boost, Multi Channel Interleaved etc with over 20KHz switching performance. TO3P package provide super low thermal resistance for much wider SOA for system stability.

Features

- Maximum Junction Temperature : $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.7\text{ V(Typ.) @ } I_C = 50\text{ A}$
- 100% of the Parts Tested for ILM(1)
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{GE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Pack age Type
FGA5065ADF	Pb-free Halide free	Active	650	50	1.7	2.1	0.309	1.35	192	-	72.2	-	-	268	Yes	TO-3P-3L

For more information please contact your local sales support at www.onsemi.com.

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